MOSFETs Silicon Carbide N-Channel MOS

TW123V65C

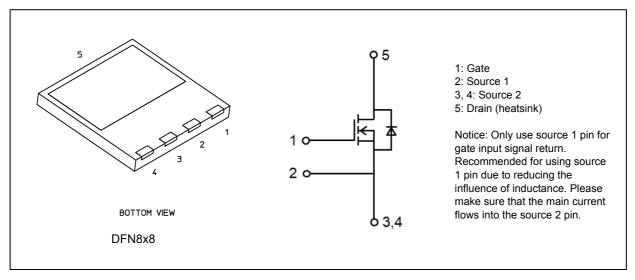
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: $V_{DSF} = -1.35 V$ (typ.)
- (3) High voltage: $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 123 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 1.2 mA)
- (6) Recommended gate source drive voltage: $V_{GS_{on}} = 18 \text{ V}, V_{GS_{off}} = 0 \text{ V}$
- (7) Enhancement mode.

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

C	Characteristics	Symbol	Rating	Unit	
Drain-source voltage			V _{DSS}	650	V
Gate-source voltage			V _{GSS}	+25/-10	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	Ι _D	18	A
Drain current (DC)	(T _c = 100°C)	(Note 1)	Ι _D	13	
Drain current (pulsed)	(T _c = 25 °C)	(Note 1)	I _{DP}	44	
Drain current (pulsed)	(T _c = 100°C)	(Note 1)	I _{DP}	34]
Power dissipation	(T _c = 25°C)		PD	76	w
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance		1.950	°C/W

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = +25/-10 V, V _{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current		I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V		2.0	25	
			T _a = 150 °C, V _{DS} = 650 V, V _{GS} = 0 V	—	10	—	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 4 mA, V _{GS} = 0 V	650		_	V
Gate threshold voltage	(Note 2)	V _{th}	V _{DS} = 10 V, I _D = 1.2 mA	3.0	_	5.0	
Drain-source on-resistance		R _{DS(ON)}	V _{GS} = 18 V, I _D = 10 A		123	183	mΩ
			T _a = 150 °C, V _{GS} = 18 V, I _D = 10 A	_	132	_	

Note 2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 400 V, V _{GS} = 0 V,	_	600	_	pF
Reverse transfer capacitance	C _{rss}]f = 100 kHz		3.7	—	
Output capacitance	C _{oss}]		80	_]
Effective output capacitance (energy related)	C _{o(er)}		_	90	_	
Effective output capacitance (time related)	C _{o(tr)}		_	128	_	
Output charge	Q _{oss}			51	_	nC
C _{oss} stored energy	E _{oss}			7.2	_	μJ
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz		11	_	Ω
Turn-on delay time	t _{d(on)}	See Fig. 6.2.1	_	21	_	ns
Switching time (rise time)	tr	-		14	_	1
Turn-off delay time	t _{d(off)}			31	_	1
Switching time (fall time)	t _f			15		
Turn-on switching loss	Eon		_	71	_	μJ
Turn-off switching loss	E _{off}]		25	_	1

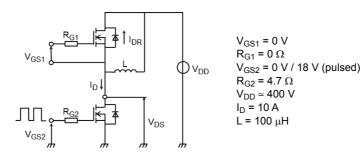


Fig. 6.2.1 Switching Time Test Circuit

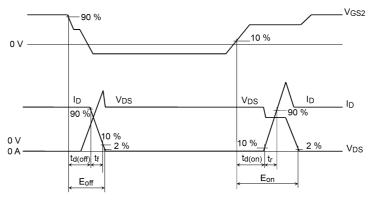


Fig. 6.2.2 Timing Diagrams

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

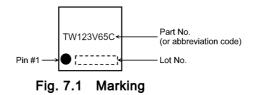
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 18 \text{ V},$ $I_D = 10 \text{ A}$	—	21	—	nC
Gate-source charge 1	Q _{gs1}		_	12	_	
Gate-drain charge	Q _{gd}			2.3		

6.4. Source \cdot Drain Characteristics (T_a = 25 °C unless otherwise specified)

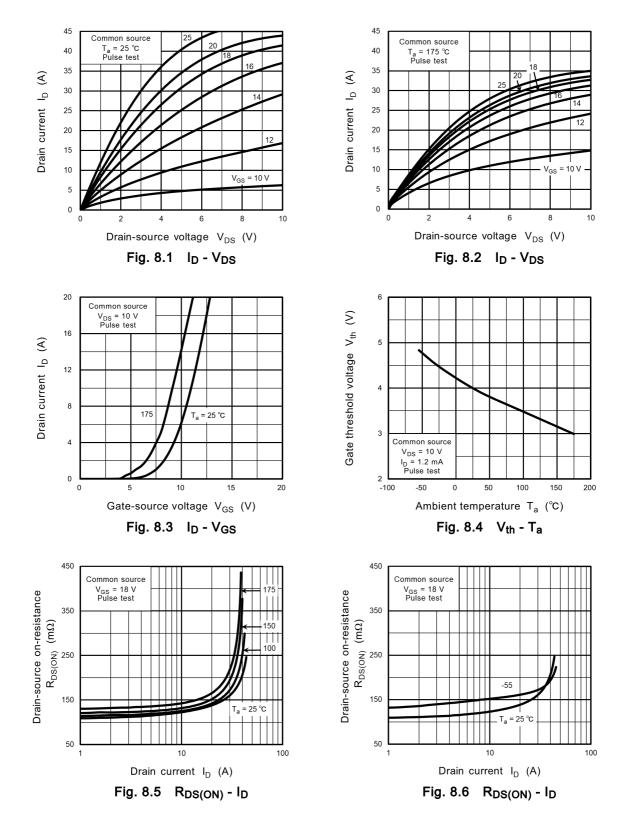
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 3)	I _{DR}	T _c = 25 °C, V _{GS} = -5 V	_	_	18	А
			T _c = 100 °C, V _{GS} = -5 V	_	—	12	
			T _c = 25 °C, V _{GS} = 18 V	—	_	18	
			T _c = 100 °C, V _{GS} = 18 V	_	_	13	
Reverse drain current	(Note 3)	I _{DRP}	T _c = 25 °C, V _{GS} = -5 V	_	_	44	
(pulsed)			T _c = 100 °C, V _{GS} = -5 V	_	_	24	
			T _c = 25 °C, V _{GS} = 18 V	_	_	44	
			T _c = 100 °C, V _{GS} = 18 V	—		34	
Diode forward voltage		V _{DSF}	I _{DR} = 5 A, V _{GS} = -5 V	—	-1.35	-1.80	V
			T _a = 150 °C, I _{DR} = 5 A, V _{GS} = -5 V	—	-1.60	—	
Reverse recovery time		t _{rr}	I _{DR} = 7 A, V _{GS} = 0 V,	_	38	_	ns
Reverse recovery charge		Q _{rr}	V _{DD} = 400 V, -dI _{DR} /dt = 1000 A/μs	—	137	_	nC
Peak reverse recovery current		I _{rr}		—	7.2	_	A

Note 3: Ensure that the channel temperature does not exceed 175 °C.

7. Marking



8. Characteristics Curves (Note)





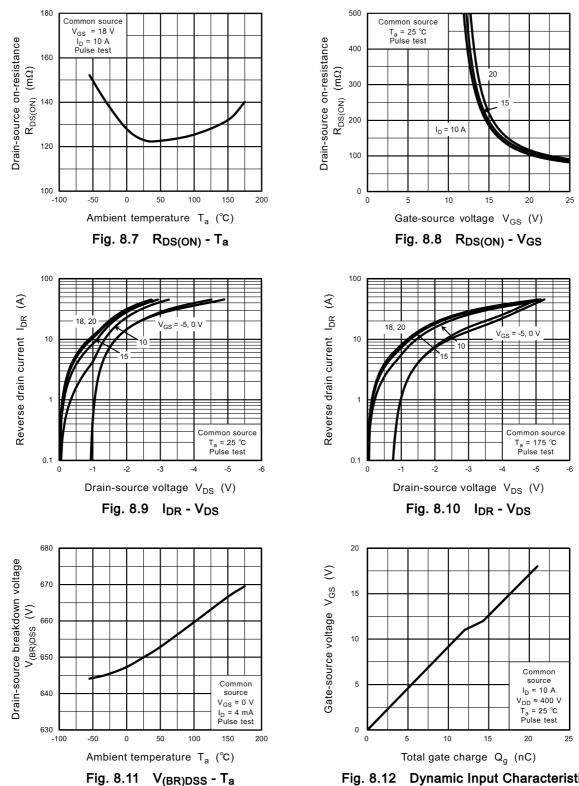
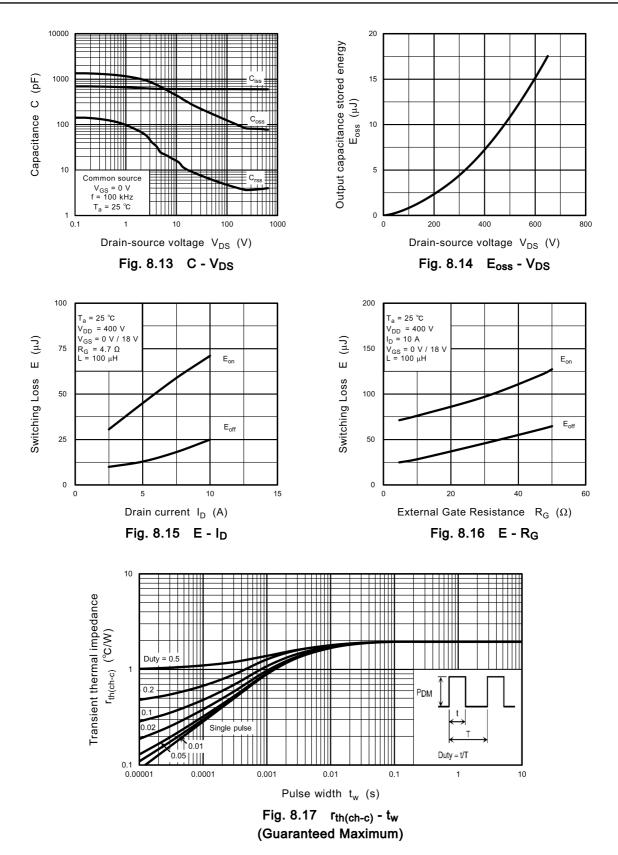
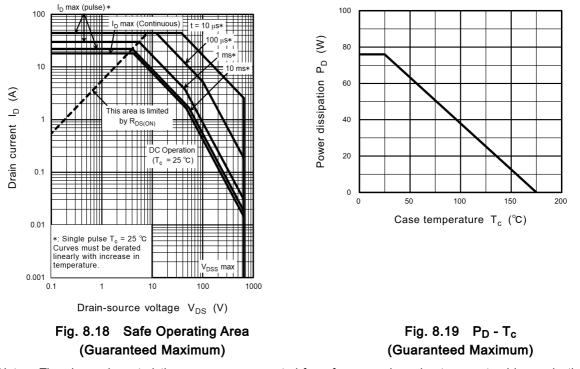


Fig. 8.12 Dynamic Input Characteristics





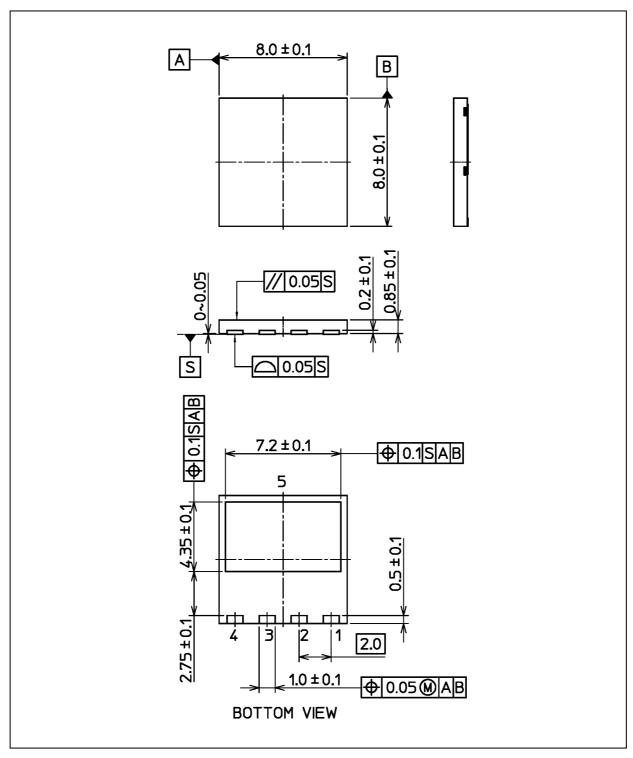
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TW123V65C

Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

Package Name(s)

TOSHIBA: 2-8T1A

Nickname: DFN8x8

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